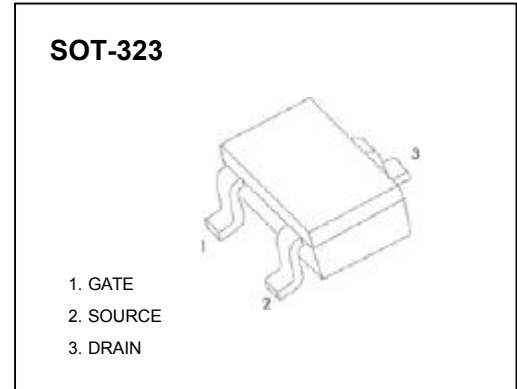


Plastic-Encapsulate MOSFETS

P-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-20V	520 mΩ@-4.5V	-0.66A
	700mΩ@-2.5V	
	950 mΩ(TYP)@-1.8V	



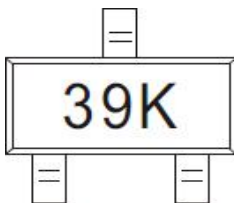
FEATURE

- Lead Free Product is Acquired
- Surface Mount Package
- P-Channel Switch with Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive

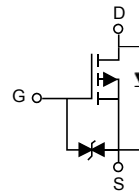
APPLICATION

- Load/Power Switching
- Interfacing, Logic Switching
- Battery Management for Ultra Small Portable Electronics

MARKING



Equivalent Circuit



Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Typical Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current (note 1)	I_D	-0.66	A
Pulsed Drain Current ($t_p=10 \mu\text{s}$)	I_{DM}	-1.2	A
Power Dissipation (note 1)	P_D	150	mW
Thermal Resistance from Junction to Ambient (note 1)	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$			-1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 20	μA
Gate threshold voltage (note 2)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.35		-1.1	V
Drain-source on-resistance (note 2)	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -1A$			520	m Ω
		$V_{GS} = -2.5V, I_D = -0.8A$			700	m Ω
		$V_{GS} = -1.8V, I_D = -0.5A$		950		m Ω
Forward transconductance (note 2)	g_{FS}	$V_{DS} = -10V, I_D = -0.54A$		1.2		S
Diode forward voltage	V_{SD}	$I_S = -0.5A, V_{GS} = 0V$			-1.2	V
DYNAMIC CHARACTERISTICS (note 4)						
Input capacitance	C_{iss}	$V_{DS} = -16V, V_{GS} = 0V, f = 1MHz$		113	170	pF
Output capacitance	C_{oss}			15	25	pF
Reverse transfer capacitance	C_{rss}			9	15	pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time (note 3)	$t_{d(on)}$	$V_{GS} = -4.5V, V_{DS} = -10V,$ $I_D = -200mA, R_{GEN} = 10\Omega$		9		ns
Turn-on rise time (note 3)	t_r			5.8		ns
Turn-off delay time (note 3)	$t_{d(off)}$			32.7		ns
Turn-off fall time (note 3)	t_f			20.3		ns

Notes :

1. Surface mounted on FR4 board using the minimum recommended pad size.
2. Pulse Test : Pulse Width=300 μs , Duty Cycle=2%.
3. Switching characteristics are independent of operating junction temperatures.
4. Guaranteed by design, not subject to producing.



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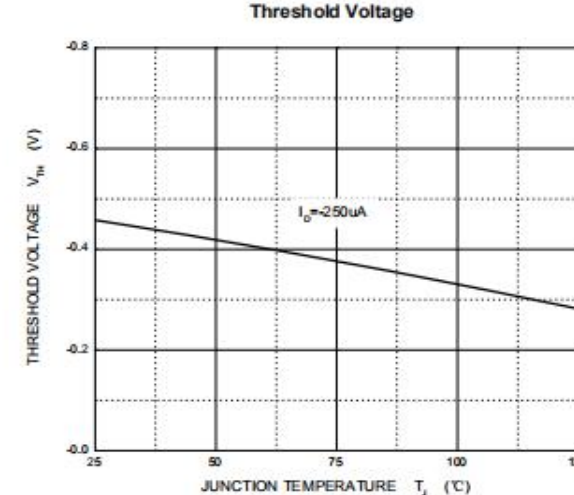
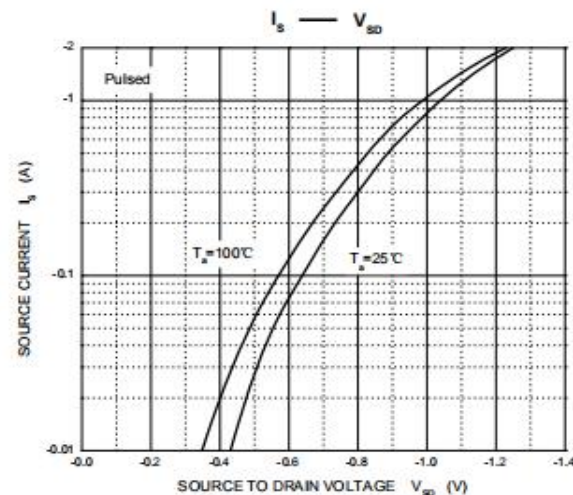
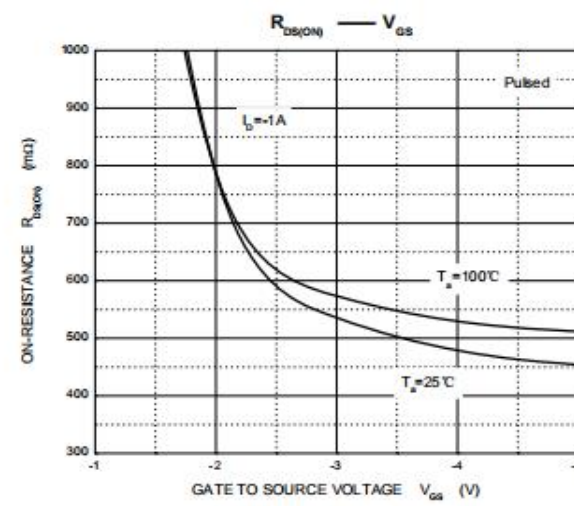
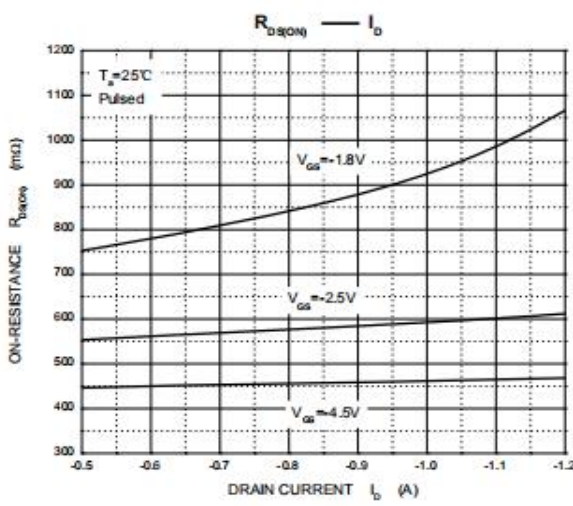
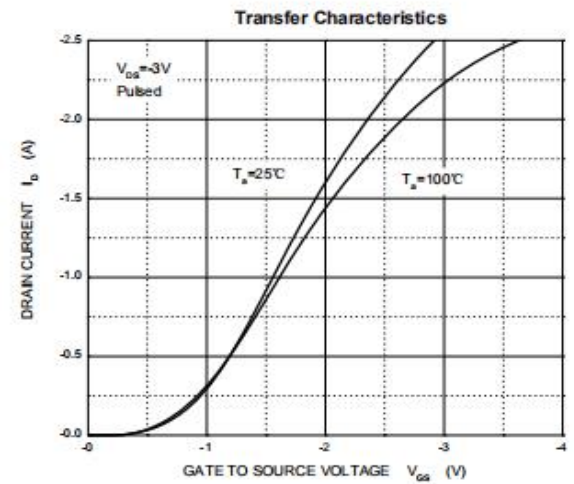
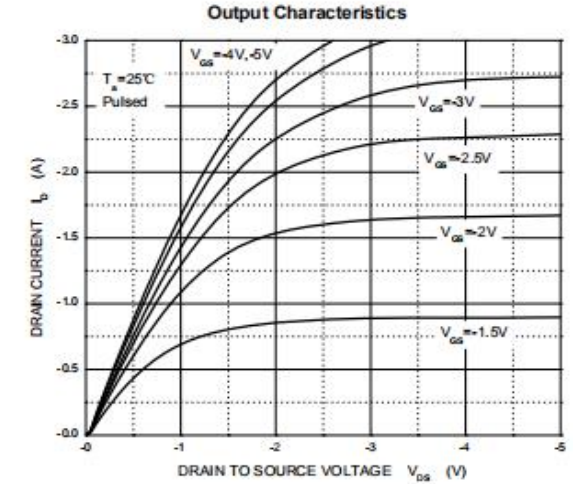
SOT-323

BC3139KW



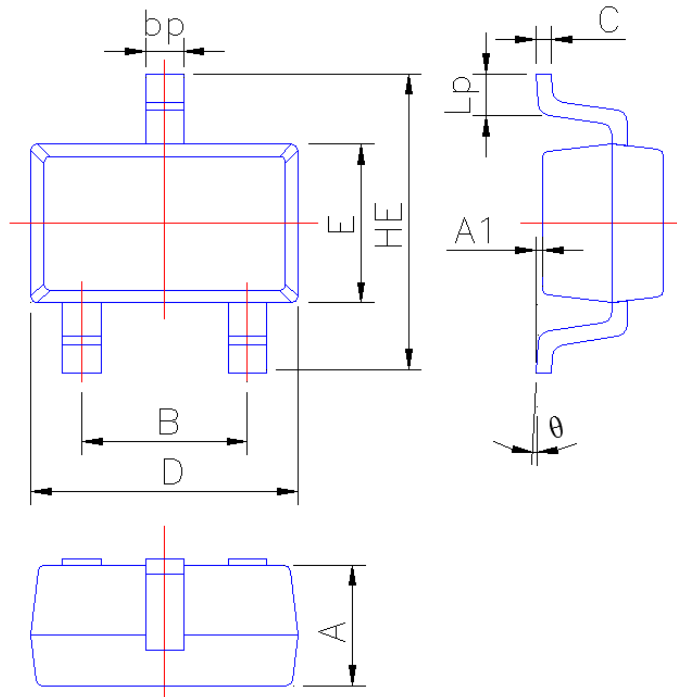
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Typical Characteristics





SOT-323 Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
θ	0°	6°